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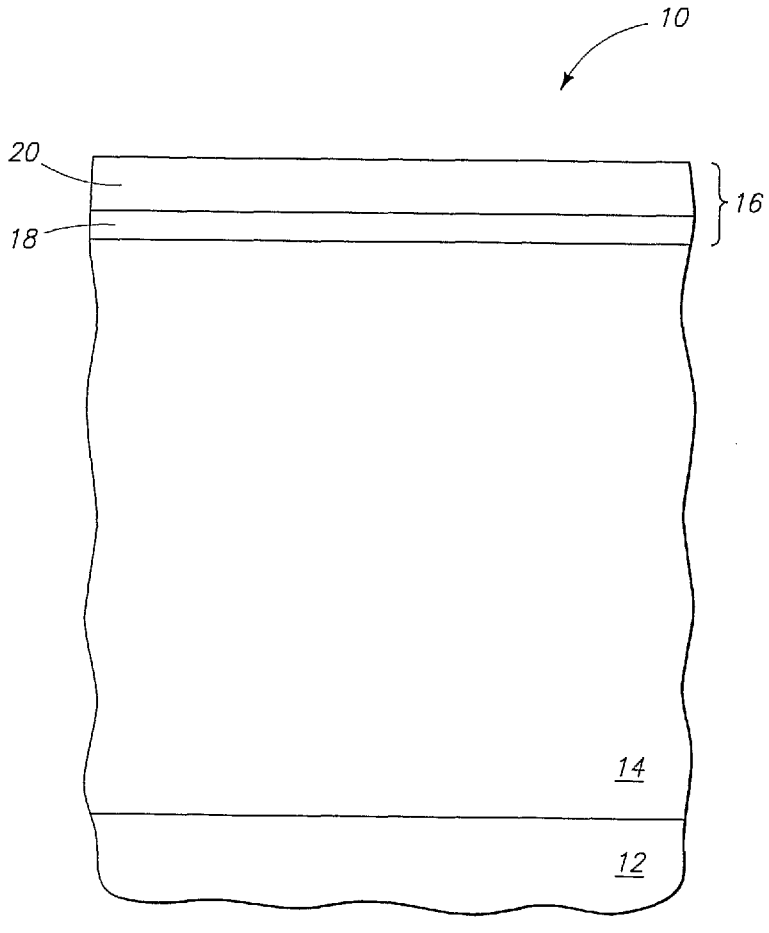
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(54) Title: METHODS OF FORMING OPENINGS INTO DIELECTRIC MATERIAL



(57) Abstract: This invention includes methods of forming openings into dielectric material. In one implementation, an opening is partially etched through dielectric material, with such opening comprising a lowest point and opposing sidewalls of the dielectric material. At least respective portions of the opposing sidewalls within the opening are lined with an electrically conductive material. With such electrically conductive material over said respective portions within the opening, plasma etching is conducted into and through the lowest point of the dielectric material of the opening to extend the opening deeper within the dielectric material. Other aspects and implementations are contemplated.

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